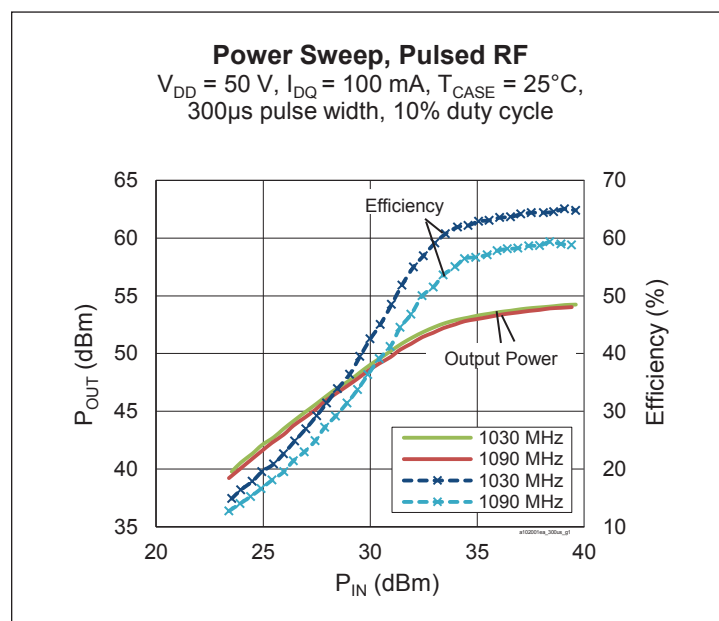


Thermally-Enhanced High Power RF LDMOS FET 200 W, 50 V, 960 – 1400 MHz

Description

The PTVA102001EA is a 200-watt LDMOS FET intended for use in power amplifier applications in the 960 – 1400 MHz frequency band. Features include high gain and thermally-enhanced package with bolt-down flange. Manufactured with Infineon's advanced LDMOS process, this device provides excellent thermal performance and superior reliability.

PTVA102001EA
Package H-36265-2



Features

- Input matched
- Capable of handling 10:1 VSWR @50 V, 200 W (CW) output power
- Integrated ESD protection
- Low thermal resistance
- Pb-free and RoHS compliant

RF Characteristics

Pulsed RF Performance (tested in Infineon production test fixture)

$V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$, $P_{OUT} = 200\text{ W}$, $f = 1090\text{ MHz}$, 300 μs pulse width, 10% duty cycle

Characteristic	Symbol	Min	Typ	Max	Unit
Gain	G_{ps}	17	18.5	—	dB
Drain Efficiency	η_D	56	59.5	—	%

All published data at $T_{CASE} = 25^\circ\text{C}$ unless otherwise indicated

ESD: Electrostatic discharge sensitive device—observe handling precautions!

RF Characteristics

Typical RF Performance (not subject to production test, verified by design/characterization in Infineon test fixture)

$V_{DD} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$, Input signal ($t_r = 5\text{ ns}$, $t_f = 6.5\text{ ns}$), $T_{CASE} = 25^\circ\text{C}$, class AB test

Mode of Operation	f (MHz)	IRL (dB)	P _{1dB}			P _{3dB}			P _{droop} (pulse) @ 200 W	t _r (ns)	t _f (ns)
			Gain (dB)	Eff (%)	P _{OUT} (W)	Gain (dB)	Eff (%)	P _{OUT} (W)			
300 μs , 10% Duty Cycle	1030	-10	18.5	60	204	16.5	62	240	0.10	6.0	7.9
1 ms, 10% Duty Cycle	1030	-10	18.3	60	200	16.3	62	235	0.20	-	-
20 ms, 10% Duty Cycle	1030	-10	18.2	59	195	16.2	61	225	0.25	-	-
16 ms, 50% Duty Cycle	1030	-10	18.2	58	190	16.2	60	215	0.30	-	-

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}$, $I_{DS} = 10\text{ mA}$	$V_{(BR)DSS}$	105	—	—	V
Drain Leakage Current	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	1	μA
	$V_{DS} = 111\text{ V}$, $V_{GS} = 0\text{ V}$	I_{DSS}	—	—	10	μA
Gate Leakage Current	$V_{GS} = 10\text{ V}$, $V_{DS} = 0\text{ V}$	I_{GSS}	—	—	1	μA
On-State Resistance	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.1\text{ V}$	$R_{DS(on)}$	—	0.34	—	Ω
Operating Gate Voltage	$V_{DS} = 50\text{ V}$, $I_{DQ} = 100\text{ mA}$	V_{GS}	3.1	3.35	3.5	V

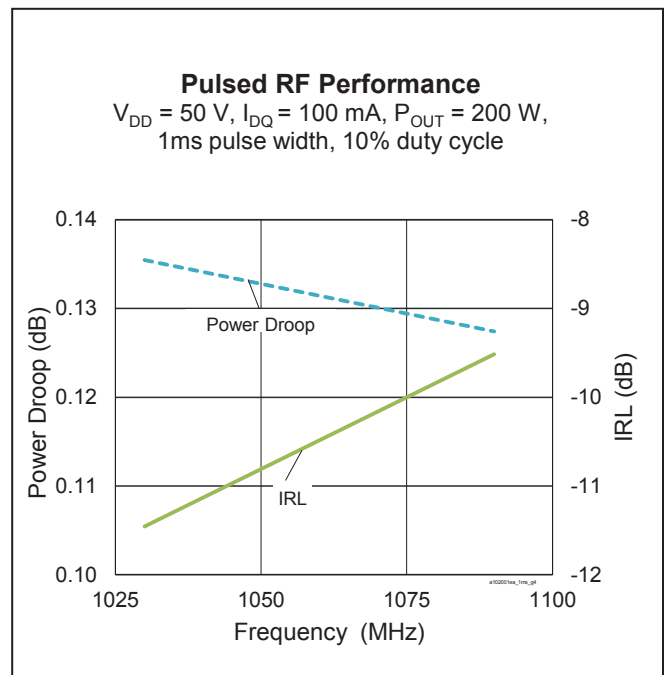
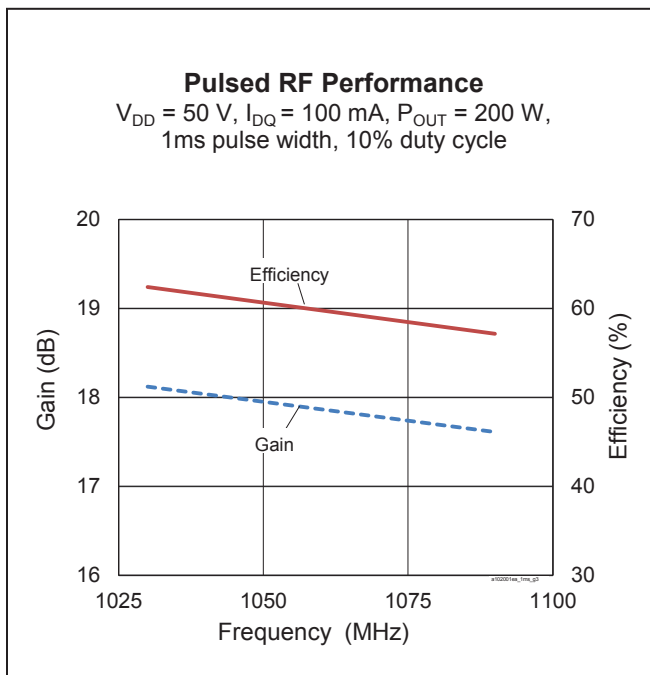
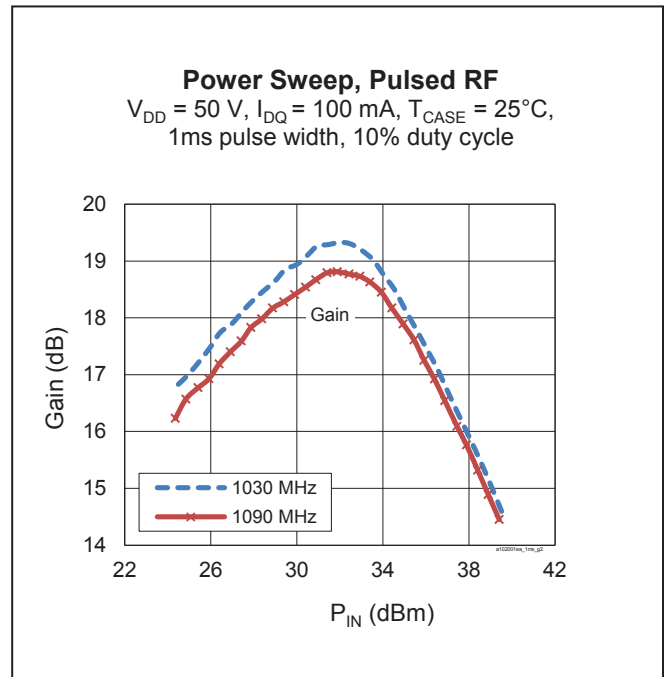
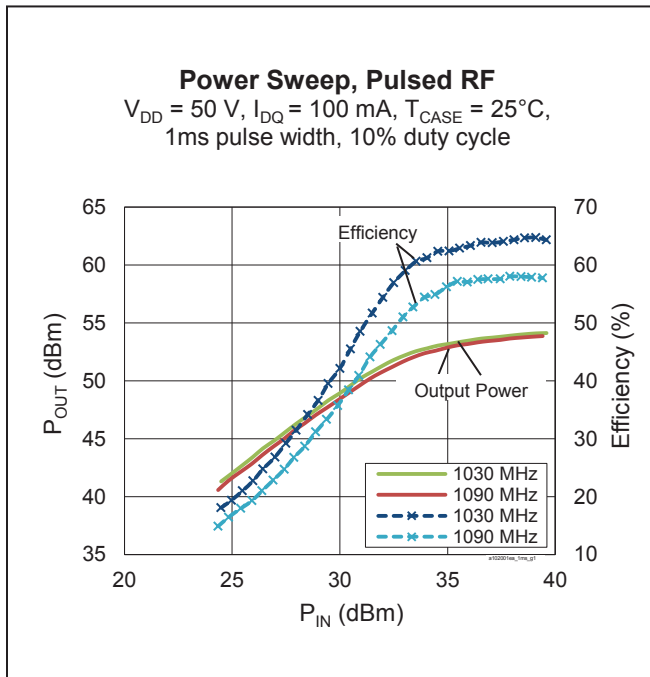
Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	105	V
Gate-Source Voltage	V_{GS}	-6 to +12	V
Operating Voltage	V_{DD}	0 to +55	V
Junction Temperature	T_J	225	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to +150	$^\circ\text{C}$
Thermal Resistance ($T_{CASE} = 70^\circ\text{C}$, 155 W CW)	$R_{\theta JC}$	0.67	$^\circ\text{C/W}$

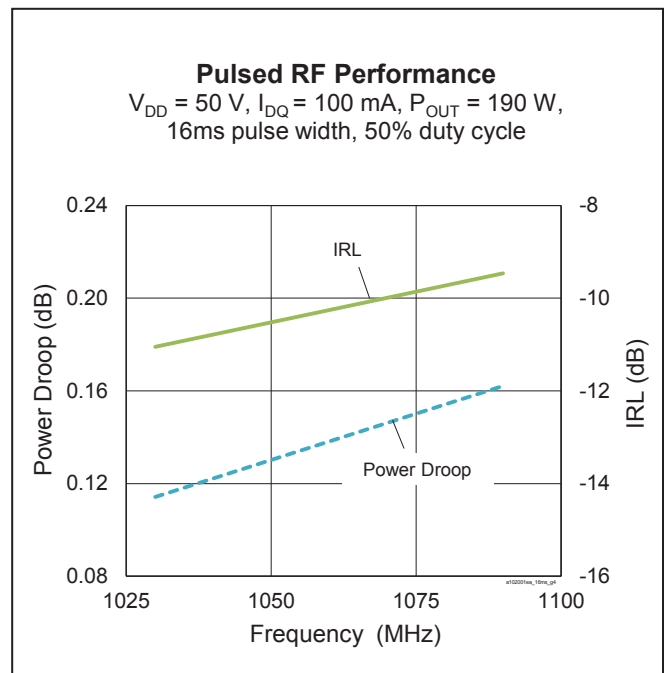
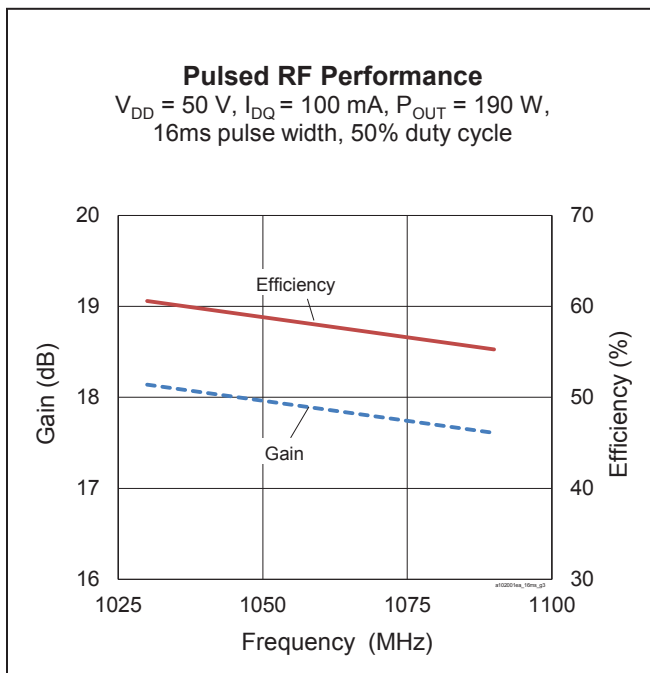
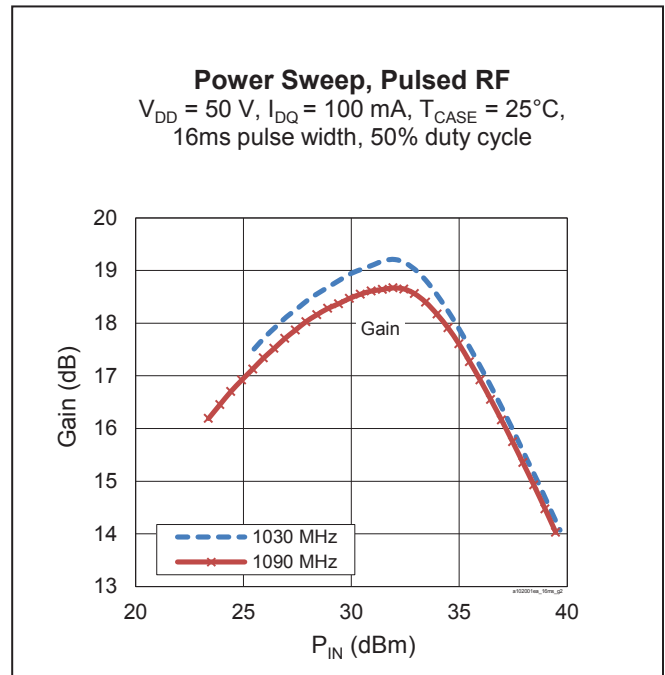
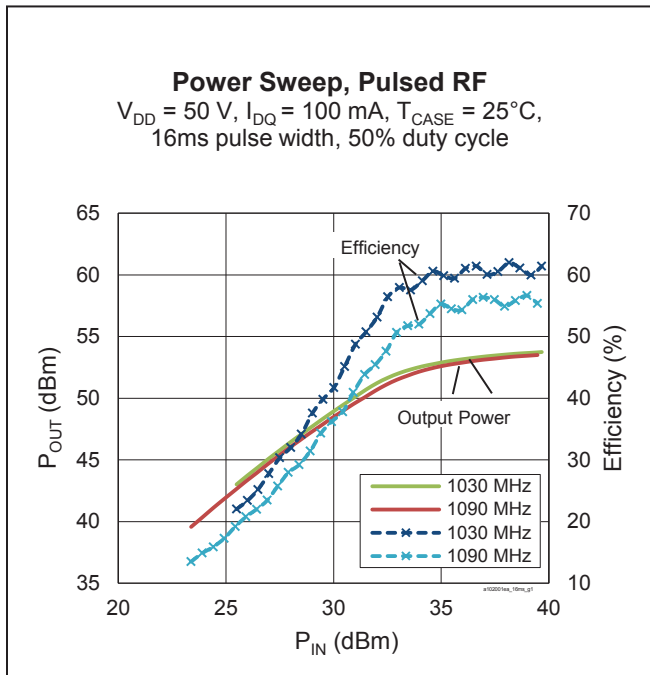
Ordering Information

Type and Version	Order Code	Package Description	Shipping
PTVA102001EA V1 R0	PTVA102001EAV1R0XTMA1	H-36265-2, bolt-down	Tape & Reel, 50 pcs
PTVA102001EA V1 R2	PTVA102001EAV1R2XTMA1	H-36265-2, bolt-down	Tape & Reel, 250 pcs

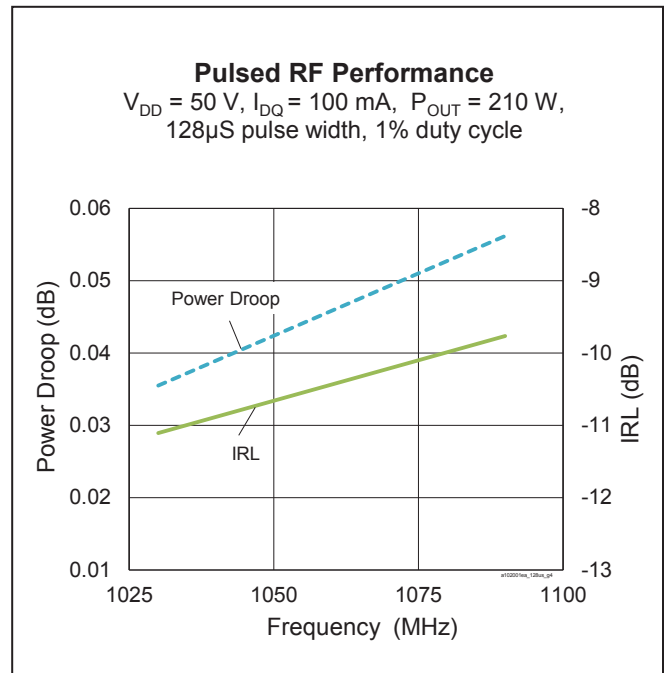
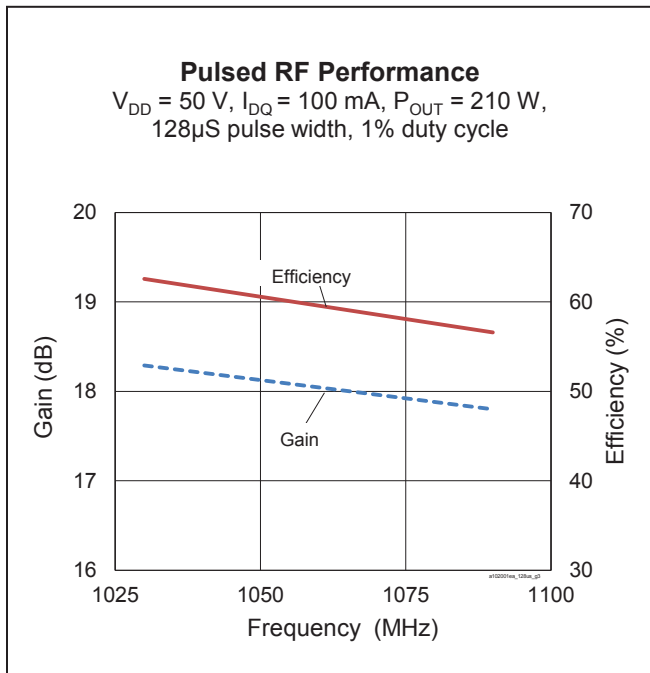
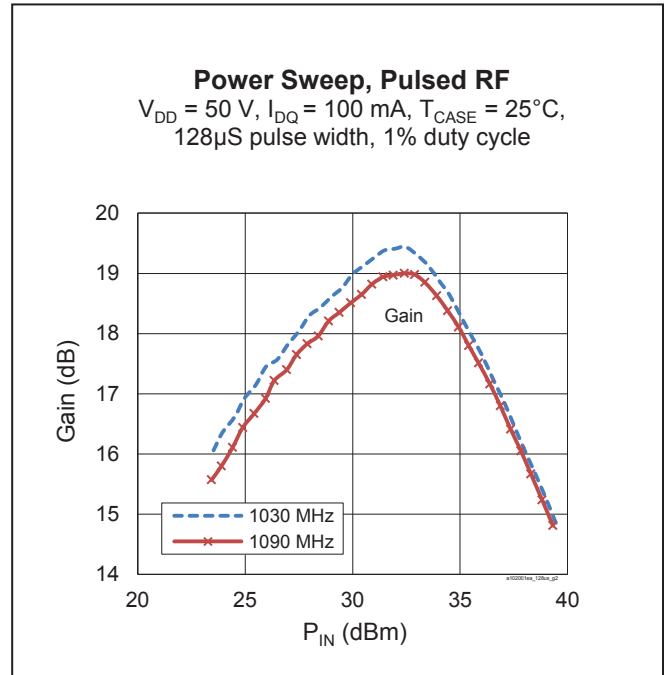
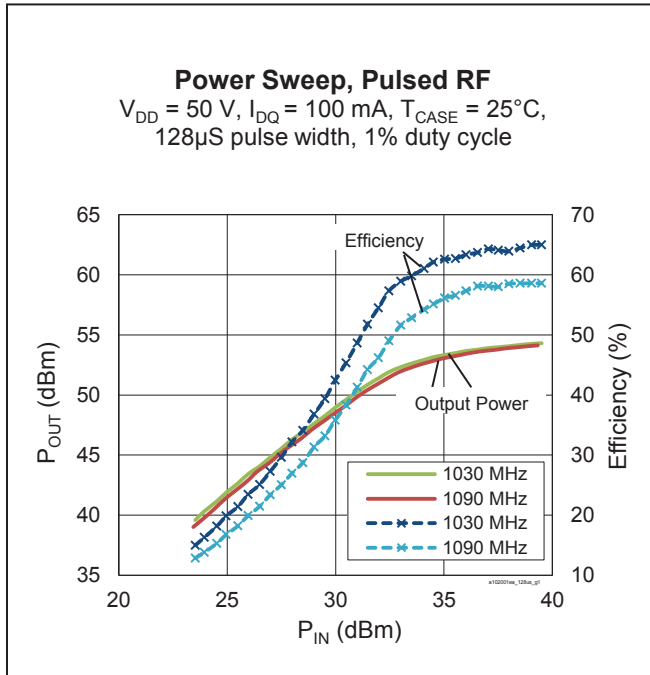
Typical RF Performance (data taken in production test fixture)



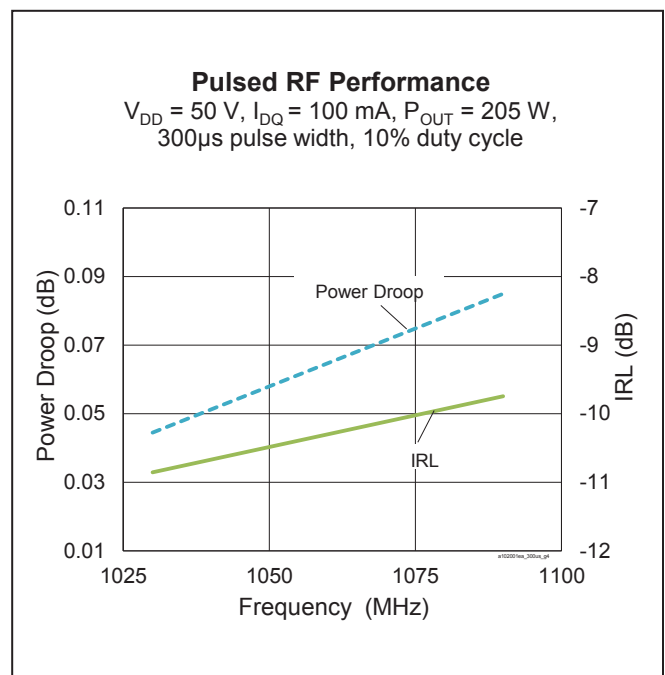
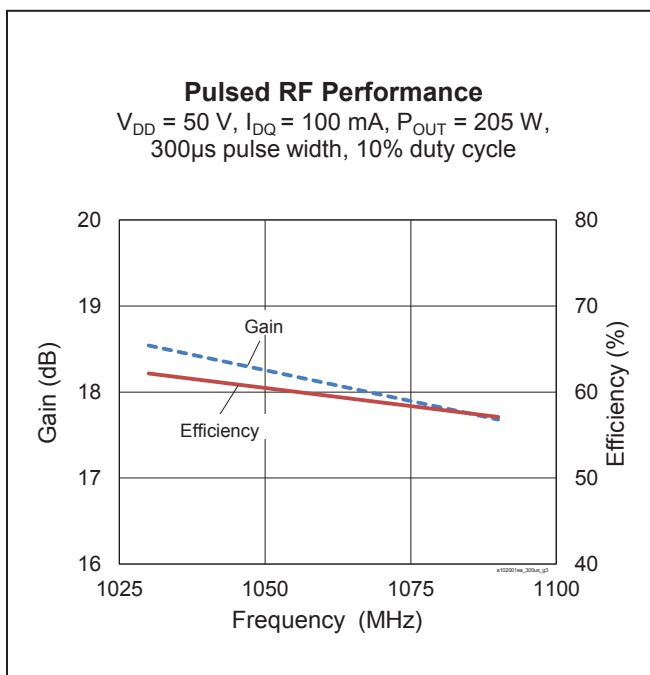
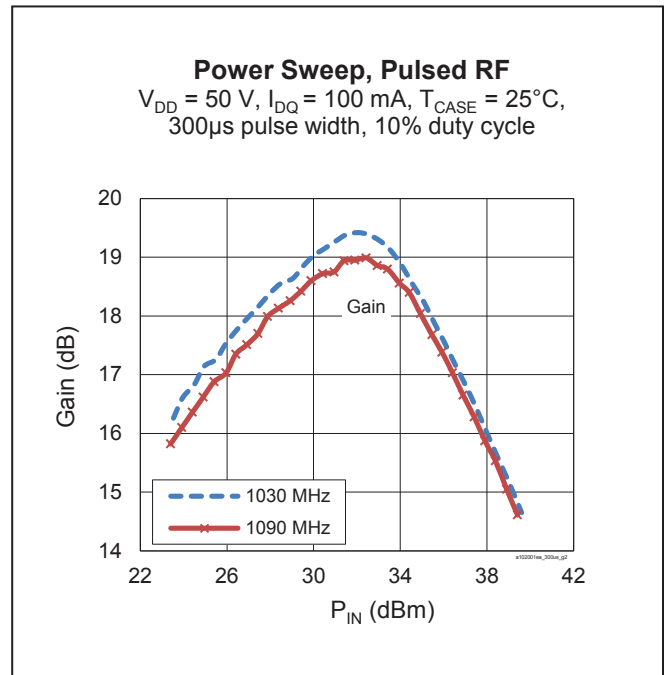
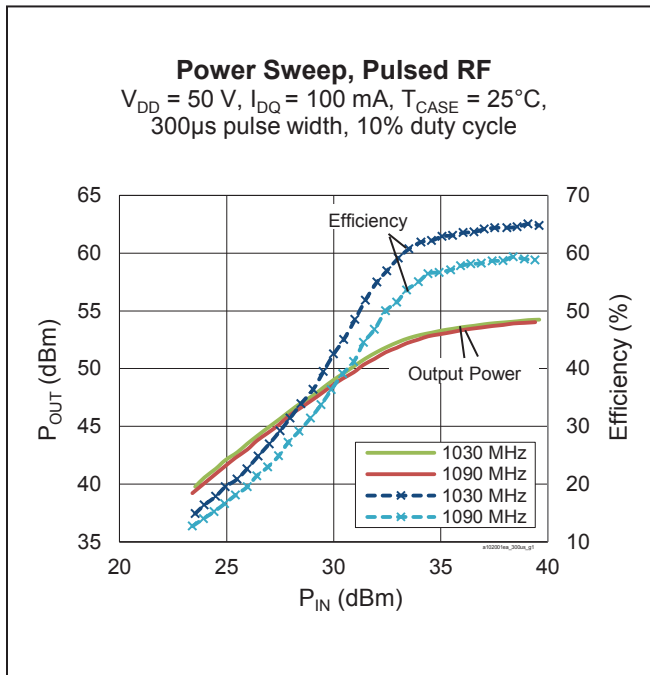
Typical RF Performance (cont.)



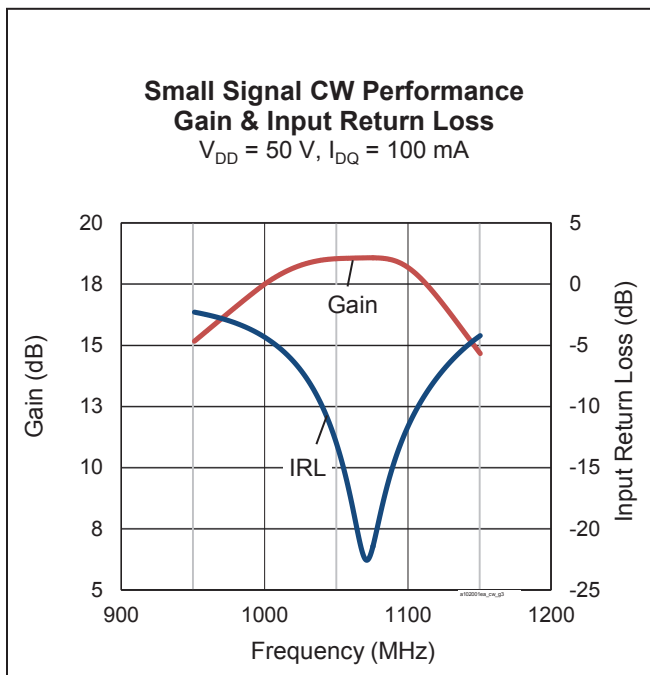
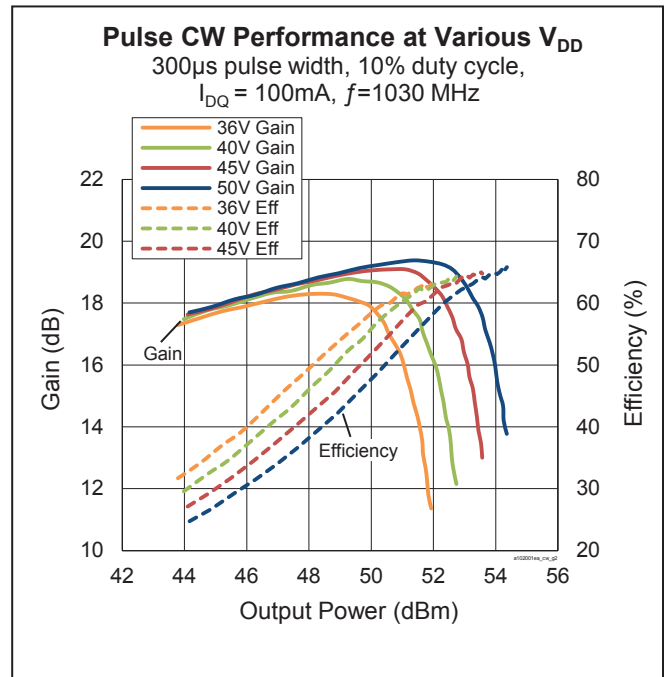
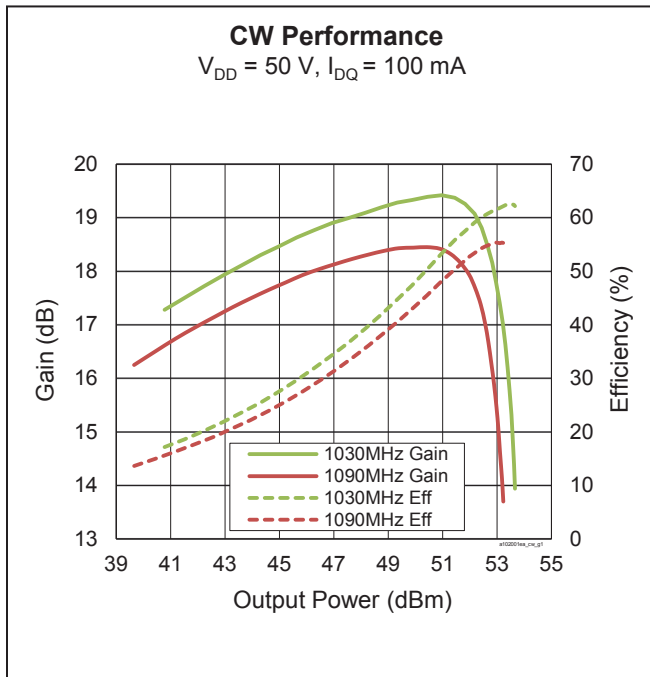
Typical RF Performance (cont.)



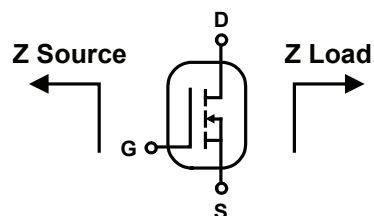
Typical RF Performance (cont.)



Typical RF Performance (cont.)



Load Pull Performance



Load Pull at Max P_{OUT} Point – 16 μ s pulse width, 10% duty cycle, class AB, $V_{DD} = 50$ V, $I_{DQ} = 90$ mA

Freq [MHz]	Z_{IN} [Ω]	P_{OUT} [dBm]	P_{OUT} [W]	P_G [dB]	PAE Eff [%]	Z_{OUT} [Ω]
960	0.97-j4.50	54.99	315.50	16.56	59.80	2.04-j0.34
1030	1.25-j5.26	54.59	287.74	15.63	57.47	2.26-j0.43
1090	1.80-j5.85	54.53	283.79	15.64	58.87	1.77-j0.33
1150	2.37-j7.11	54.53	283.79	15.23	56.97	2.04-j0.65
1200	2.51-j6.97	54.31	269.77	15.13	55.28	2.09-j0.67
1300	4.92-j7.48	54.55	285.10	14.70	56.37	1.80-j0.99
1400	7.37-j5.29	54.39	274.98	14.09	54.45	1.45-j1.14

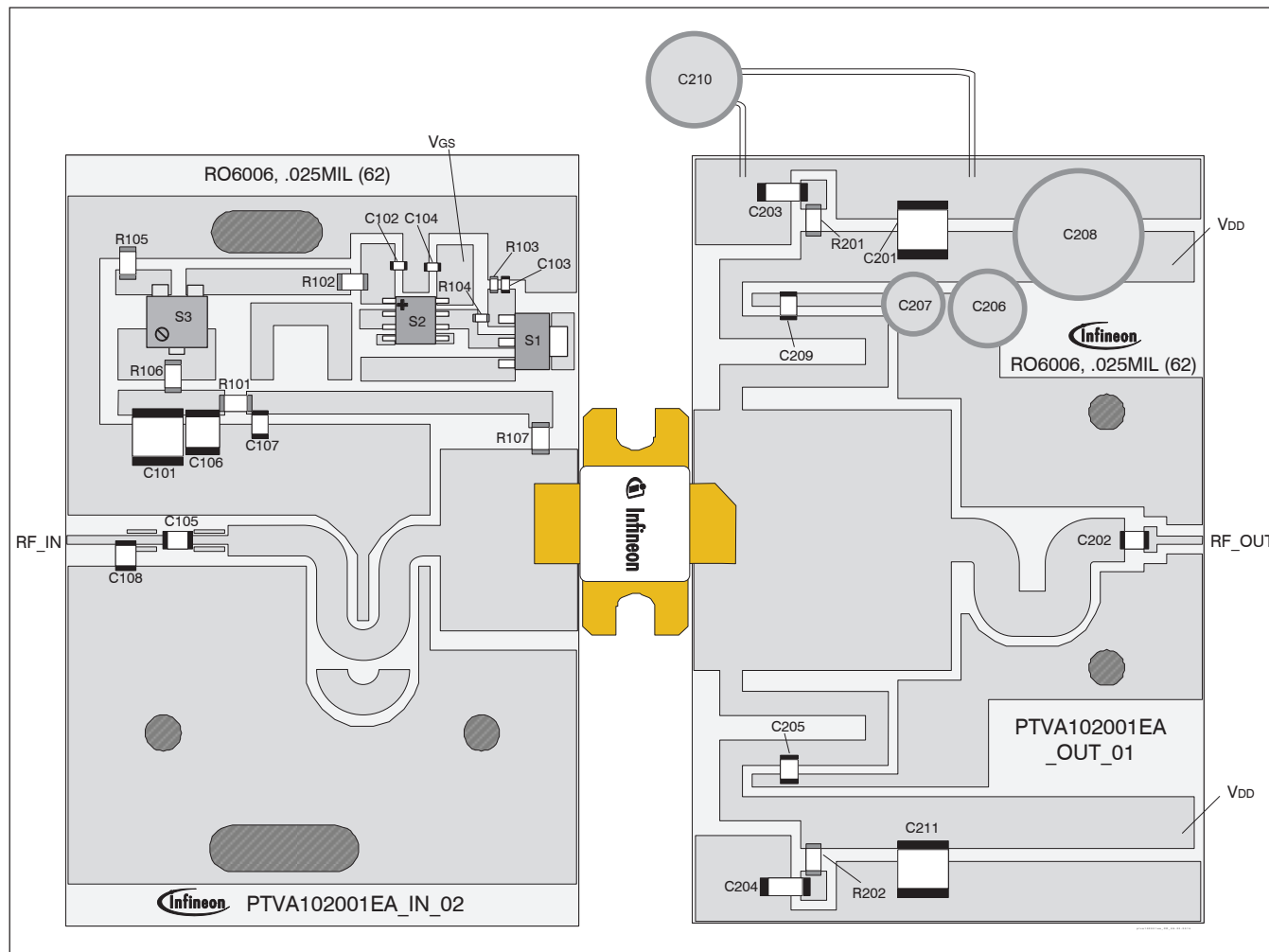
Load Pull at Max Efficiency Point – 16 μ s pulse width, 10% duty cycle, class AB, $V_{DD} = 50$ V, $I_{DQ} = 90$ mA

Freq [MHz]	Z_{IN} [Ω]	P_{OUT} [dBm]	P_{OUT} [W]	P_G [dB]	PAE Eff [%]	Z_{OUT} [Ω]
960	0.97-j4.50	53.57	227.51	18.32	69.97	1.73+j1.19
1030	1.25-j5.26	53.42	219.79	17.35	67.24	1.63+j0.98
1090	1.80-j5.85	53.38	217.77	17.14	67.31	1.50+j0.72
1150	2.37-j7.11	53.47	222.18	16.82	65.81	1.41+j0.42
1200	2.51-j6.97	52.40	173.78	17.04	65.40	1.08+j0.60
1300	4.92-j7.48	53.17	207.49	16.41	65.45	1.17-j0.02
1400	7.37-j5.29	53.25	211.35	15.61	62.61	0.92-j0.51

Z Optimum – 16 μ s pulse width, 10% duty cycle, class AB, $V_{DD} = 50$ V, $I_{DQ} = 90$ mA

Freq [MHz]	Z_{IN} [Ω]	P_{OUT} [dBm]	P_{OUT} [W]	P_G [dB]	PAE Eff [%]	Z_{OUT} [Ω]
960	0.97-j4.50	54.51	282.49	17.55	67.45	1.94+j0.54
1030	1.25-j5.26	54.18	261.82	16.79	65.13	1.85+j0.51
1090	1.80-j5.85	54.17	261.22	16.54	65.34	1.71+j0.28
1150	2.37-j7.11	54.12	258.23	16.28	63.89	1.65+j0.04
1200	2.51-j6.97	53.78	238.78	16.23	62.92	1.48+j0.06
1300	4.92-j7.48	53.99	250.61	15.79	62.33	1.54-j0.32
1400	7.37-j5.29	53.76	237.68	15.19	61.07	1.10-j0.64

Reference Circuit, 1030 – 1090 MHz



Reference Circuit (cont.)

Reference Circuit Assembly

DUT	PTVA102001EA
Test Fixture Part No.	LTN/PTVA102001EA V1
PCB	Rogers 6006, 0.635 mm [0.025"] thick, 2 oz. copper, $\epsilon_r = 6.15$, $f = 1030 - 1090$ MHz

Components Information

Component	Description	Suggested Manufacturer	P/N
Input			
C101	Capacitor, 10 μ F	TDK Corporation	C5750X5R1H106K230KA
C102, C103, C104	Capacitor, 1000 pF	Panasonic Electronic Components	ECJ-1VB1H102K
C105, C107	Capacitor, 39 pF	ATC	ATC100B390KW500XB
C106	Capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C108	Capacitor, 3.6 pF	ATC	ATC100B3R6CW500XB
R101	Resistor, 5.6 Ω	Panasonic Electronic Components	ERJ-8RQJ5R6V
R102, R107	Resistor, 10 Ω	Panasonic Electronic Components	ERJ-8GEYJ100V
R103	Resistor, 1.3K Ω	Panasonic Electronic Components	ERJ-3GEYJ132V
R104	Resistor, 1.2K Ω	Panasonic Electronic Components	ERJ-3GEYJ122V
R105	Resistor, 2000 Ω	Panasonic Electronic Components	ERJ-8GEYJ202V
R106	Resistor, 1000 Ω	Panasonic Electronic Components	ERJ-8GEYJ102V
S1	Transistor	Infineon Technologies	BCP56
S2	Voltage Regulator	Texas Instruments	LM78L05ACM
S3	Potentiometer, 2k Ω	Bourns Inc.	3224W-1-202E
Output			
C201, C211	Capacitor, 10 μ F	TDK Corporation	C5750X5R1H106K230KA
C202, C205, C209	Capacitor, 39 pF	ATC	ATC100B390KW500XB
C203, C204	Capacitor, 1 μ F	TDK Corporation	C4532X7R2A105M230KA
C206	Capacitor, 22 μ F	Cornell Dubilier Electronics (CDE)	SEK220M100ST
C207	Capacitor, 10 μ F	Cornell Dubilier Electronics (CDE)	SEK100M100ST
C208	Capacitor, 100 μ F	Cornell Dubilier Electronics (CDE)	SK101M100ST
C210	Capacitor, 6800 μ F	Panasonic Electronic Components	ECO-S2AP682EA
R201, R202	Resistor, 5.6 Ω	Panasonic Electronic Components	ERJ-8RQJ5R6V

Package Outline Specifications

Package H-36265-2

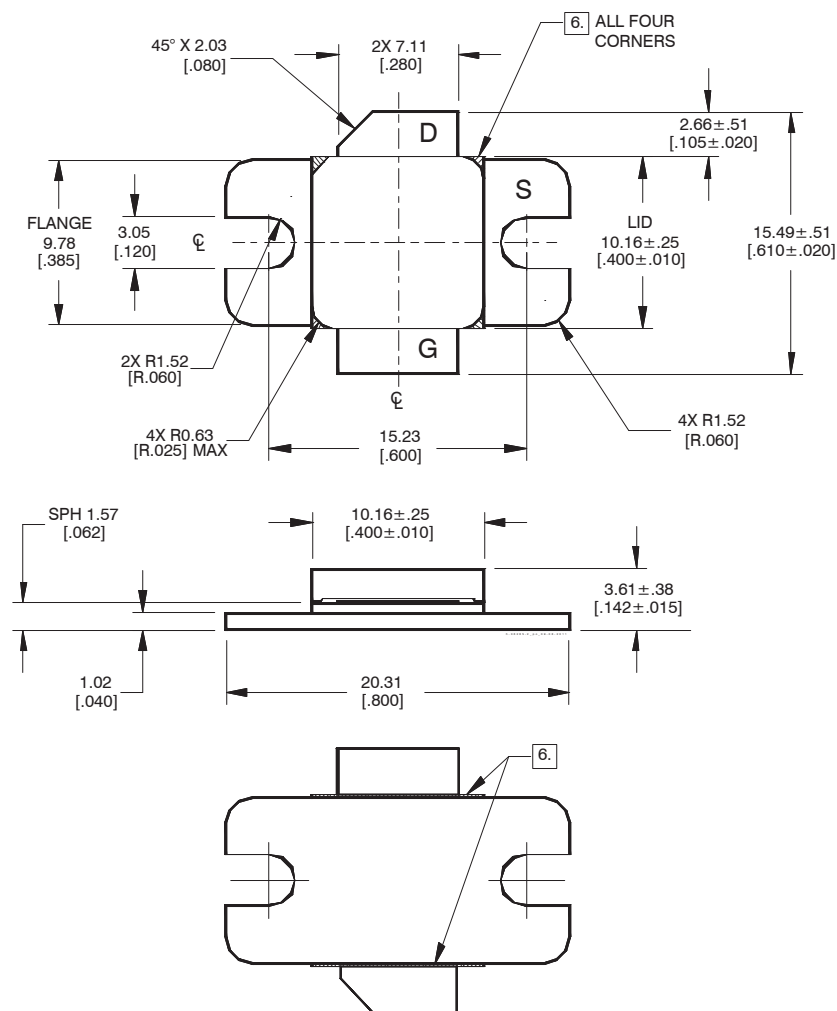


Diagram Notes—unless otherwise specified:

- Interpret dimensions and tolerances per ASME Y14.5M-1994.
- Primary dimensions are mm. Alternate dimensions are inches.
- All tolerances ± 0.127 [0.005] unless specified otherwise.
- Pins: D – drain; G – gate; S – source
- Lead thickness: $0.10 + 0.051/-0.025$ mm [0.004 + 0.002/-0.001 inch].
- Exposed metal plane on top and bottom of ceramic insulator.
- Gold plating thickness: 1.14 ± 0.38 micron [45 ± 15 microinch].

Find the latest and most complete information about products and packaging at the Infineon Internet page
<http://www.infineon.com/rfpower>

Revision History

Revision	Date	Data Sheet Type	Page	Subjects (major changes since last revision)
01	2015-07-22	Advance	All	Data Sheet reflects advance specification for product development
02	2015-09-22	Production	All	Data Sheet reflects released product specification
02.1	2017-02-08	Production	2	Updated operating voltage and junction temperature

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highpowerRF@infineon.com

To request other information, contact us at:
 +1 877 465 3667 (1-877-GO-LDMOS) USA
 or +1 408 776 0600 International



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